

Title (en)

ORGANIC THIN FILM TRANSISTOR AND METHOD OF MANUFACTURING ORGANIC THIN FILM TRANSISTOR

Title (de)

ORGANISCHER DÜNNSCHICHTTRANSISTOR UND VERFAHREN ZUR HERSTELLUNG EINES ORGANISCHEN DÜNNSCHICHTTRANSISTORS

Title (fr)

TRANSISTOR EN COUCHES MINCES ORGANIQUES ET PROCÉDÉ DE FABRICATION DE TRANSISTOR EN COUCHES MINCES ORGANIQUES

Publication

EP 3848977 B1 20240626 (EN)

Application

EP 19858491 A 20190809

Priority

- JP 2018164317 A 20180903
- JP 2019031628 W 20190809

Abstract (en)

[origin: EP3848977A1] Provided are an organic thin film transistor that has high bendability and can suppress a decrease in carrier mobility caused by a pinhole of an insulating film or leveling properties and a method of manufacturing the organic thin film transistor. The organic thin film transistor includes: a gate electrode; an insulating film that is formed to cover the gate electrode; an organic semiconductor layer that is formed on the insulating film, and a source electrode and a drain electrode that are formed on the organic semiconductor layer, in which the insulating film includes an inorganic film consisting of SiNH.

IPC 8 full level

H10K 10/46 (2023.01)

CPC (source: EP US)

H10K 10/472 (2023.02 - EP US); **H10K 10/474** (2023.02 - EP US); **H10K 71/12** (2023.02 - US); **H10K 71/18** (2023.02 - EP)

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

DOCDB simple family (publication)

EP 3848977 A1 20210714; **EP 3848977 A4 20211103**; **EP 3848977 B1 20240626**; JP 7083396 B2 20220610; JP WO2020049956 A1 20210812; US 2021184142 A1 20210617; WO 2020049956 A1 20200312

DOCDB simple family (application)

EP 19858491 A 20190809; JP 2019031628 W 20190809; JP 2020541090 A 20190809; US 202117186275 A 20210226